Improving the performance of Nb3Sn cavities requires altering the growth process to produce better films. A good understanding of how Nb3Sn grows via the Sn diffusion process is required in order to know how to modify the process to achieve a better film. Here we present experimental studies of Nb3Sn layer growth that further our understanding of the Nb3Sn growth process. This includes microscopy of samples that were grown with different substrate preparations, modified growth processes, or stopped during growth. The results are interpreted and methods proposed to prevent several forms of defects from forming (thin film regions, Sn-depleted sites, and surface roughness).

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